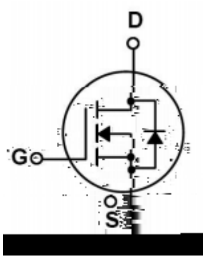
DFN2×2B-6L N MOS
N-Channel Enhancement Mode Field Effect Transistor in a DFN2×2B-6L Plastic Package.

V_{DS} (V) = 30V I_D =14.7A (V_{GS} = ± 20V)
$R_{DS(ON)}$@10V<7mΩ(Typ. 6.3mΩ)
$R_{DS(ON)}$@4.5V<12mΩ(Typ. 9.5mΩ)
HF Product.

DC/DC
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



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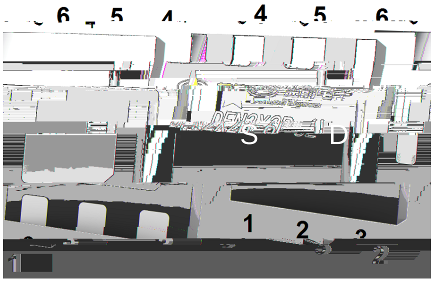

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See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Drain Current	I_D	14.7	A
Gate-Source Voltage	V_{GS}	±20	V
Power Dissipation	P_D		

/

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=15 V V_{GS}=10V R_L=0.75Ω R_{GEN}=3Ω		11		ns
Turn-On Rise Time	t_r			14		ns
Turn-Off Delay Time	$t_{d(off)}$			38		ns
Turn-Off Fall Time	t_f			10		ns

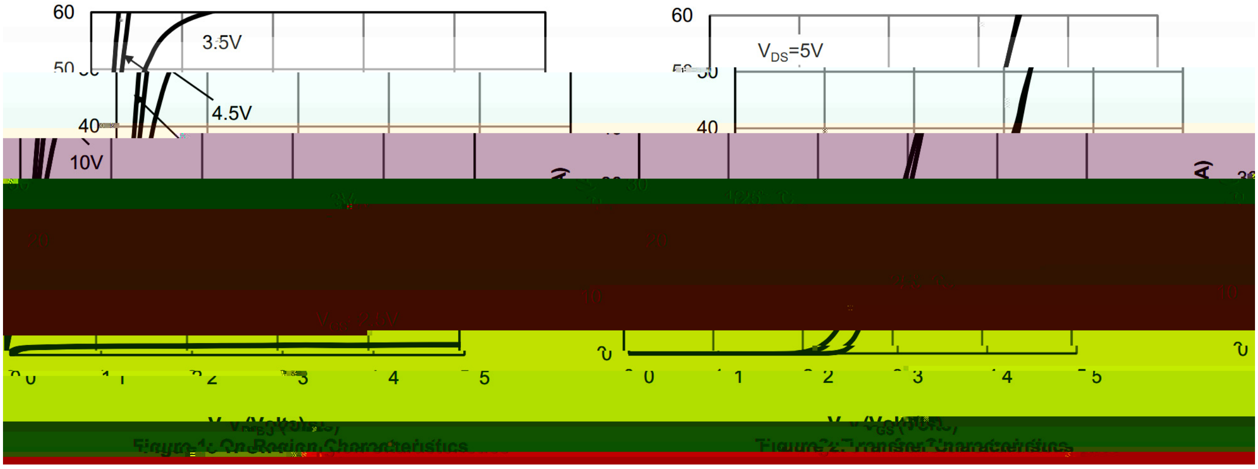
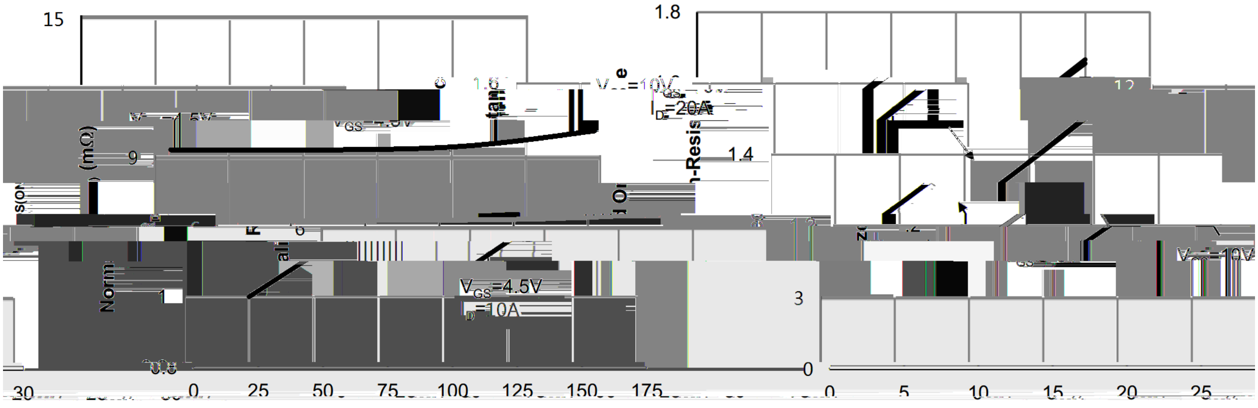
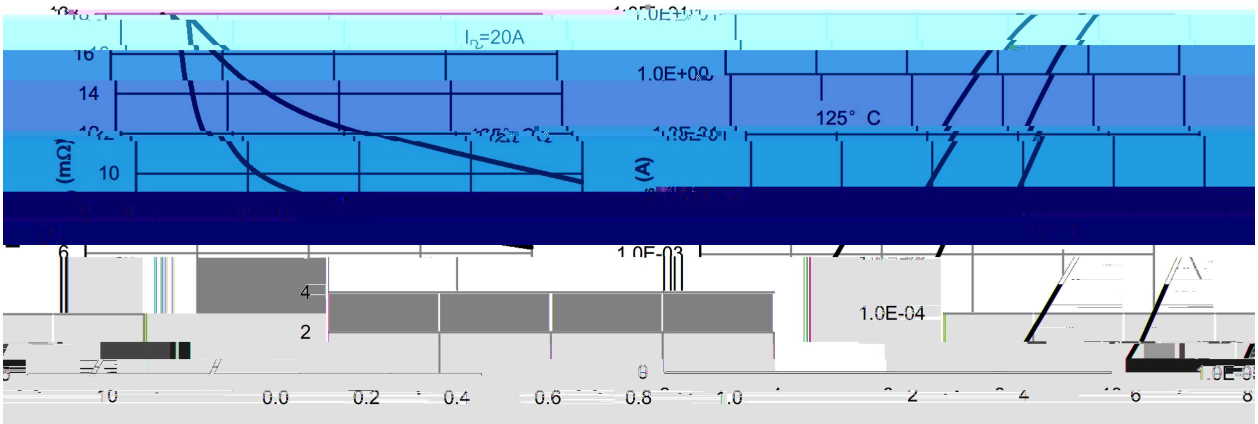


Figure 1: On-Region Characteristics Figure 2: Transfer Characteristics



Voltage



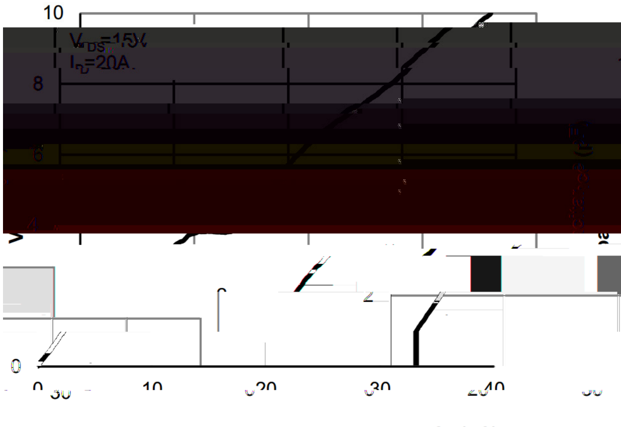


Figure 7: Gate Charge Characteristics

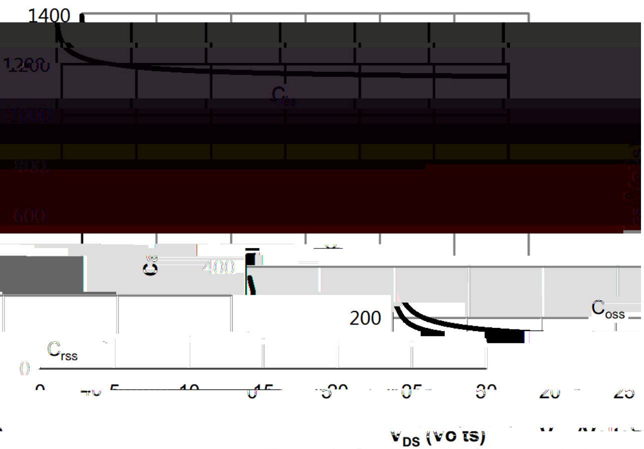


Figure 8: Capacitance Characteristics

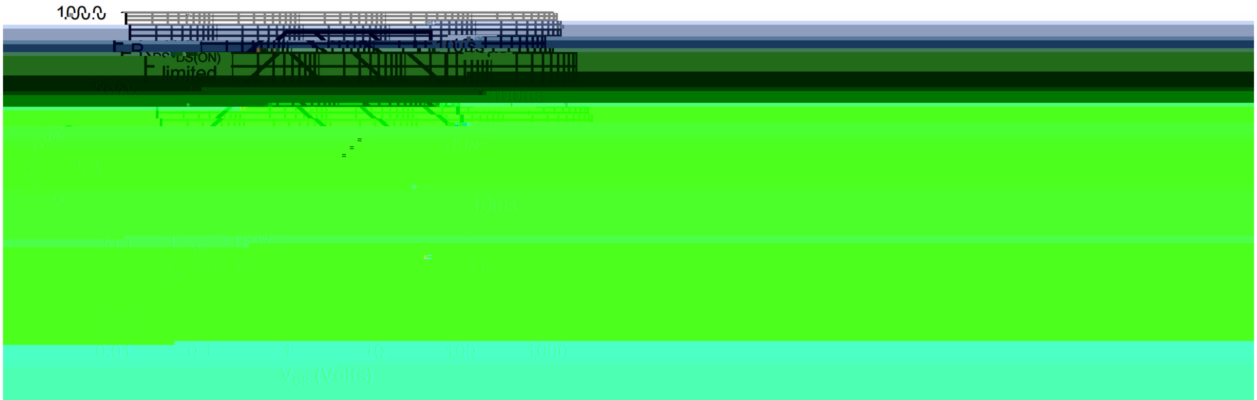
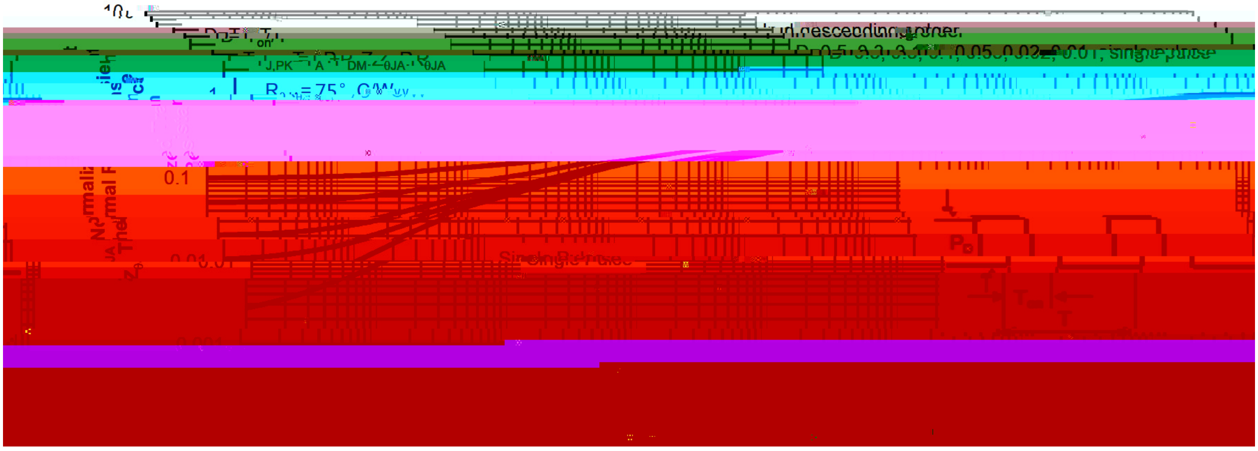
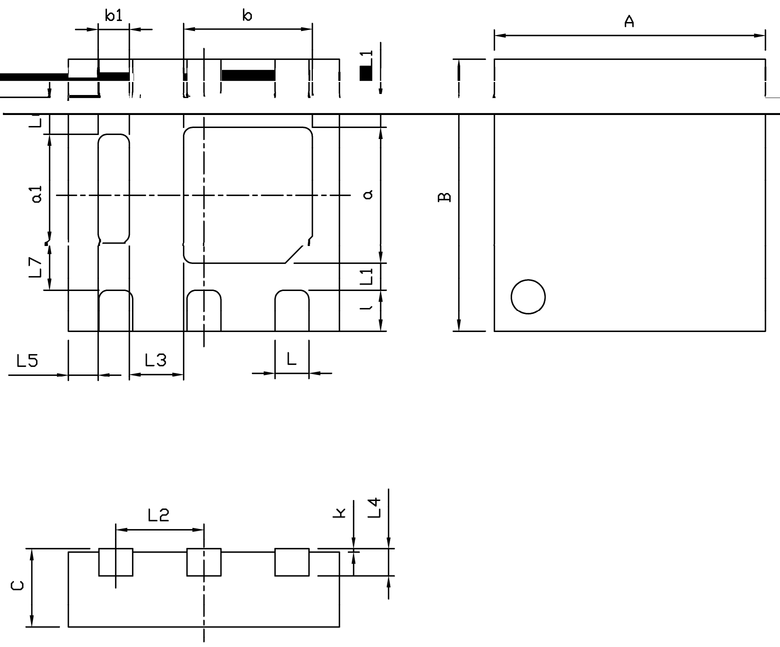


Figure 9: Maximum Forward Biased Safe Operating Area



DFN2X2B-6L-0.5

Unit:mm



Symbol	Dimensions In Millimeters MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	–	0.65	–
L3	0.30	0.40	0.50
L4	–	0.152	–
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	–	0.05

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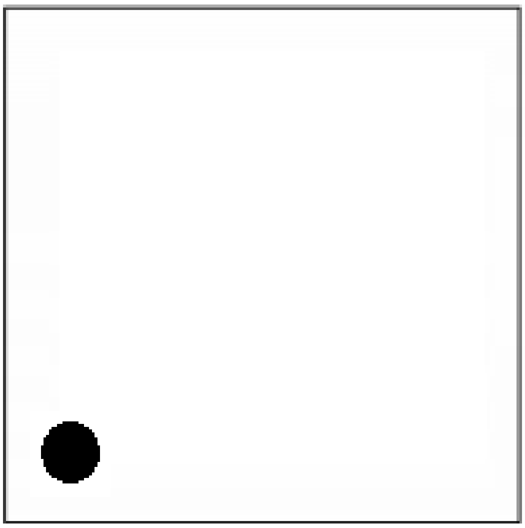

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